

Daniel Feezell

List of Publications by Year in descending order

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27
papers

1,268
citations

430754

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552653

26
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docs citations

27
times ranked

1260
citing authors

#	ARTICLE	IF	CITATIONS
1	Interfacial Impurities and Their Electronic Signatures in High-Voltage Regrown Nonpolar m -Plane GaN Vertical n -Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900757.	0.8	14
2	Defect suppression in wet-treated etched-and-regrown nonpolar m -plane GaN vertical Schottky diodes: A deep-level optical spectroscopy analysis. <i>Journal of Applied Physics</i> , 2020, 128, 185703.	1.1	3
3	Field emission scanning probe lithography with GaN nanowires on active cantilevers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 032806.	0.6	3
4	Delta-doped In^{2+} -Ga ₂ O ₃ thin films and In^{2+} -(Al _{0.26} Ga _{0.74}) ₂ O ₃ / In^{2+} -Ga ₂ O ₃ heterostructures grown by metalorganic vapor-phase epitaxy. <i>Applied Physics Express</i> , 2020, 13, 045501.		
5	A Decade of Nonpolar and Semipolar III-Nitrides: A Review of Successes and Challenges. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800628.	0.8	54
6	Electrically Injected GHz-Class GaN/InGaN Core-Shell Nanowire-Based LEDs: Carrier Dynamics and Nanoscale Homogeneity. <i>ACS Photonics</i> , 2019, 6, 1618-1625.	3.2	52
7	Si-doped In^{2+} -(Al _{0.26} Ga _{0.74}) ₂ O ₃ thin films and heterostructures grown by metalorganic vapor-phase epitaxy. <i>Applied Physics Express</i> , 2019, 12, 111004.	1.1	47
8	Thermal and efficiency droop in InGaN/GaN light-emitting diodes: decoupling multiphysics effects using temperature-dependent RF measurements. <i>Scientific Reports</i> , 2019, 9, 19921.	1.6	19
9	Carrier Dynamics in InGaN/GaN Micro-LEDs: An RF Approach to Understand Efficiency Issues. , 2019, , .		0
10	Insufficiency of the Young's modulus for illustrating the mechanical behavior of GaN nanowires. <i>Nanotechnology</i> , 2018, 29, 205706.	1.3	11
11	Nonpolar m -Plane InGaN/GaN Micro-Scale Light-Emitting Diode With 1.5 GHz Modulation Bandwidth. <i>IEEE Electron Device Letters</i> , 2018, 39, 520-523.	2.2	93
12	Invention, development, and status of the blue light-emitting diode, the enabler of solid-state lighting. <i>Comptes Rendus Physique</i> , 2018, 19, 113-133.	0.3	89
13	Sharp GaN nanowires used as field emitter on active cantilevers for scanning probe lithography. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018, 36, .	0.6	5
14	Experimental study of field emission from ultrasharp silicon, diamond, GaN, and tungsten tips in close proximity to the counter electrode. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018, 36, .	0.6	13
15	High-Speed Nonpolar InGaN/GaN LEDs for Visible-Light Communication. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 381-384.	1.3	67
16	Explanation of low efficiency droop in semipolar (202 \AA -1 \AA) InGaN/GaN LEDs through evaluation of carrier recombination coefficients. <i>Optics Express</i> , 2017, 25, 19343.	1.7	34
17	Optical properties of Ag-coated GaN/InGaN axial and core-shell nanowire light-emitting diodes. <i>Journal of Optics (United Kingdom)</i> , 2015, 17, 025004.	1.0	14
18	Analysis of light extraction efficiency for gallium nitride-based coaxial microwall light-emitting diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 766-770.	0.8	5

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19	Optical properties of nonpolar III-nitrides for intersubband photodetectors. Journal of Applied Physics, 2013, 113, .	1.1	34
20	Optical polarization characteristics of semipolar (303Å ⁻¹) and (303Å ⁻¹ Å ⁻¹) InGaN/GaN light-emitting diodes. Optics Express, 2013, 21, A53.	1.7	35
21	High-Power, Low-Efficiency-Droop Semipolar (20ar ² ar ¹) Single-Quantum-Well Blue Light-Emitting Diodes. Applied Physics Express, 2012, 5, 062103.	1.1	102
22	Indium incorporation and emission properties of nonpolar and semipolar InGaN quantum wells. Applied Physics Letters, 2012, 100, .	1.5	168
23	Reduction in Thermal Droop Using Thick Single-Quantum-Well Structure in Semipolar (20ar ² ar ¹) Blue Light-Emitting Diodes. Applied Physics Express, 2012, 5, 102103.	1.1	41
24	Influence of polarity on carrier transport in semipolar (2021Å ⁻) and (202Å ⁻¹) multiple-quantum-well light-emitting diodes. Applied Physics Letters, 2012, 100, .	1.5	54
25	High-Power Blue-Violet Semipolar (20ar ² ar ¹) InGaN/GaN Light-Emitting Diodes with Low Efficiency Droop at 200 A/cm ² . Applied Physics Express, 2011, 4, 082104.	1.1	177
26	Influence of Mg-doped barriers on semipolar (202Å ⁻¹) multiple-quantum-well green light-emitting diodes. Applied Physics Letters, 2011, 99, 141114.	1.5	21
27	High optical polarization ratio from semipolar (202Å ⁻¹ Å ⁻) blue-green InGaN/GaN light-emitting diodes. Applied Physics Letters, 2011, 99, .	1.5	75